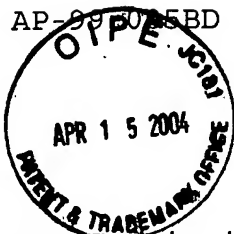


AP-89-005BD



April 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/790,578 03/01/04

Peter Lee et al.

ARRAY ARCHITECTURE AND PROCESS FLOW
OF NONVOLATILE MEMORY DEVICES FOR
MASS STORAGE APPLICATIONS

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on April 12, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 4/12/04

Atwood et al., "Intel Strata Flash TM Memory Technology Overview," Intel Technology Journal, 4th quarter 1997, pp.1-12, describes a stacked gate structure in which an ETOX process is used to produce a multiple level cell to store two bit in the same memory cell.

U.S. Patent 5,828,600 to Kato et al., "Non-Volatile Semiconductor Memory," describes a nonvolatile semiconductor memory where the cells are a MOSFET with a floating gate and have low power, high speed and reduced cell area.

U.S. Patent 5,095,344 to Harari, "Highly Compact EPROM and Flash EEPROM Devices," discloses a highly compact flash memory device using an intelligent programming technique to allow multiple bits to be stored in each cell and an intelligent erase program to extend the useful life of each cell.

U.S. Patent 5,029,130 to Yeh, "Single Transistor Non-Volatile Electrically Alterable Semiconductor Memory Device," discloses a single transistor electrically programmable and erasable memory cell using a split gate which allows the control gate to control a portion of the channel and the floating gate to control the remaining portion of the channel.

AP-99-005BD

U.S. Patent 5,400,279 to Momodomi et al., "Nonvolatile Semiconductor Memory Device with NAND Cell Structure," discloses a nonvolatile memory device with a NAND cell structure.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a stylized flourish extending from the end.

Stephen B. Ackerman,
Reg. No. 37761

